

WHAT IS CLAIMED IS:

1. A semiconductor memory device comprising:
a semiconductor substrate;
a pair of field effect transistors associated with said semiconductor
substrate wherein each source of said transistors shares a common impurity doped
region formed in a plateau elevated from said semiconductor substrate and each gate
electrode of said transistors is formed over each channel region of said transistors;
a first capacitor connected to a drain of one of said transistors;
a second capacitor connected to a drain of another one of said
transistors.
wherein said each of said first and second capacitors comprises a pair
of electrodes and a dielectric layer interposed therebetween, said dielectric layer
comprising a ferroelectric material, and
wherein each of said first and second capacitors is located over said
gate electrode of the corresponding transistor so as to completely overlap said gate
electrode.